



### CST2012S N-Ch 20V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology



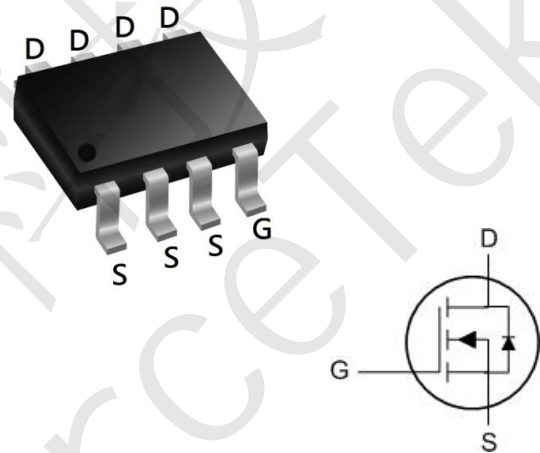
#### CST2012S Product Summary

BVDSS	RDSON	ID
20V	8mΩ	12.0A

#### CST2012S Description

The CST2012S is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The CST2012S meet the RoHS and Green Product requirement with full function reliability approved.

#### CST2012S SOP8 Pin Configuration



#### CST2012S Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	12.0	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	7.0	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	34	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	3	W
$P_D@T_A=70^\circ C$	Total Power Dissipation <sup>3</sup>	0.86	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

#### CST2012S Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	100	$^\circ C/W$



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#### CST2012S Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

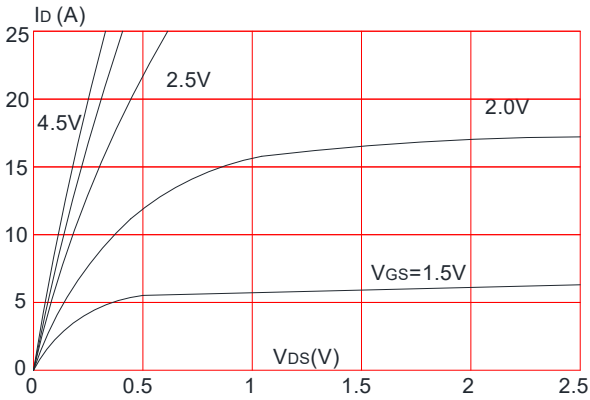
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.75	1.2	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	-	8	11.2	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =10A	-	11.7	17.5	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz	-	1000	-	pF
C <sub>oss</sub>	Output Capacitance		-	182	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	164	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =15A, V <sub>GS</sub> =4.5V	-	15	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	2	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	5.2	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =10V, I <sub>D</sub> =15A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	9	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	25	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	37	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	14	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	120	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =30A	-	-	1.2	V

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature  
 2. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=10V, V<sub>G</sub>=4.5V, L=0.5mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=9.6A  
 3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

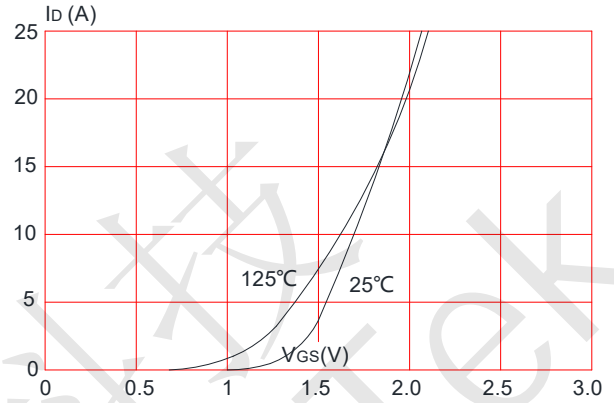


## CST2012S Typical Performance Characteristics

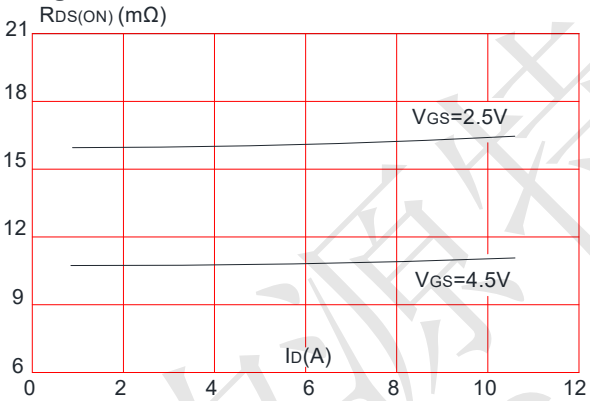
**Figure 1: Output Characteristics**



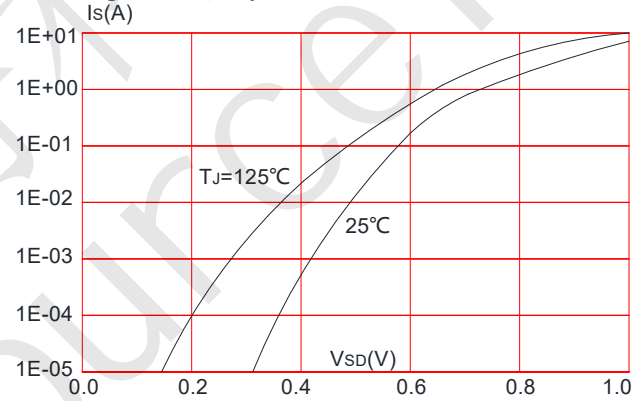
**Figure 2: Typical Transfer Characteristics**



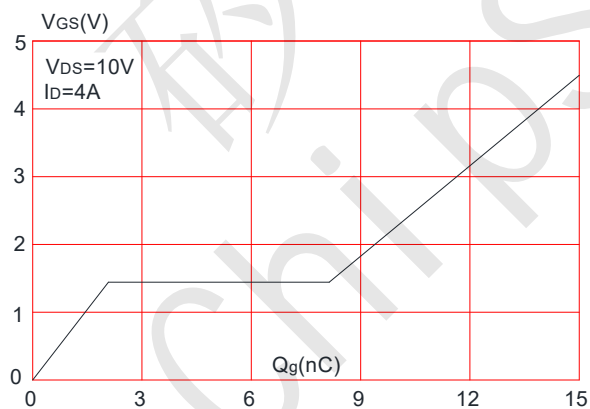
**Figure 3: On-resistance vs. Drain Current**



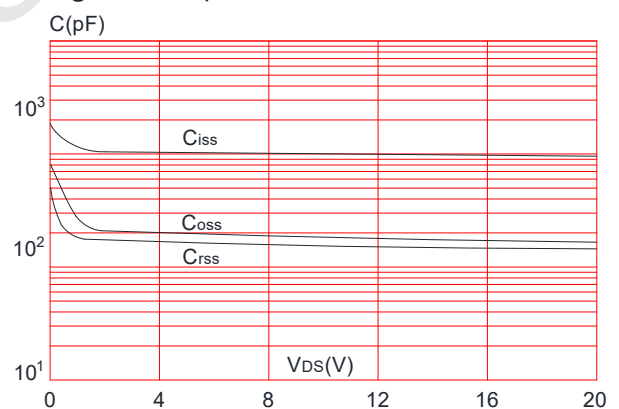
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



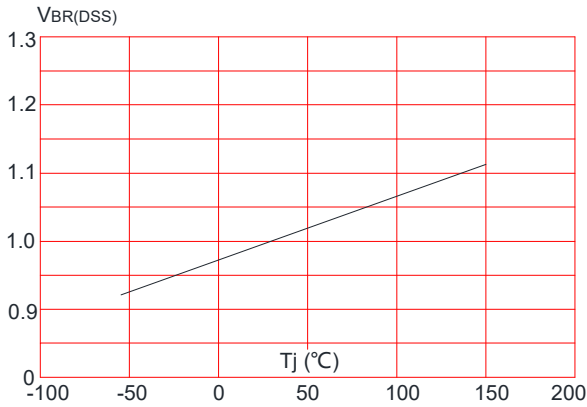
**Figure 6: Capacitance Characteristics**



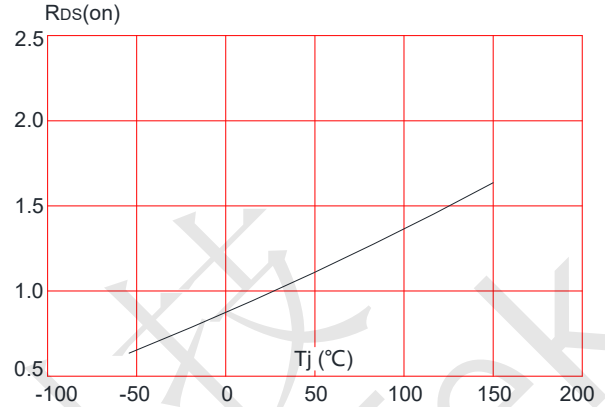


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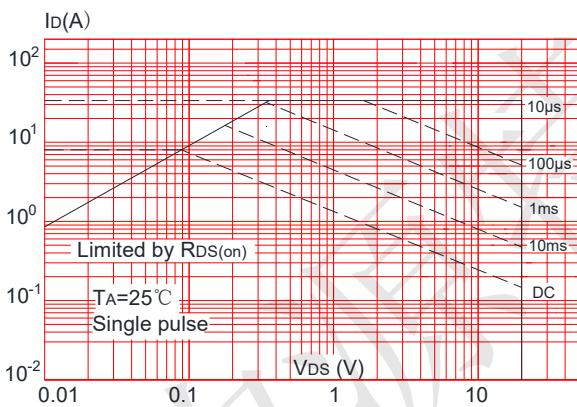
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



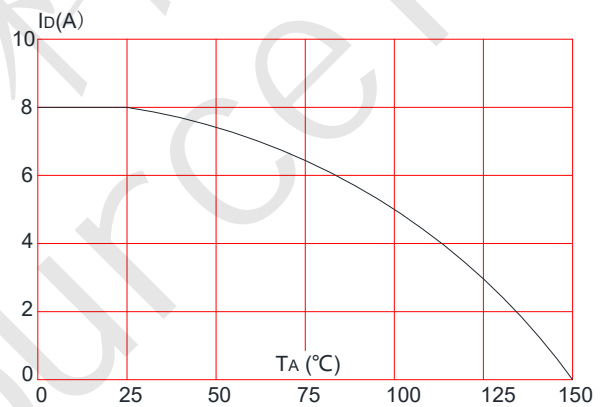
**Figure 8:** Normalized on Resistance vs. Junction Temperature



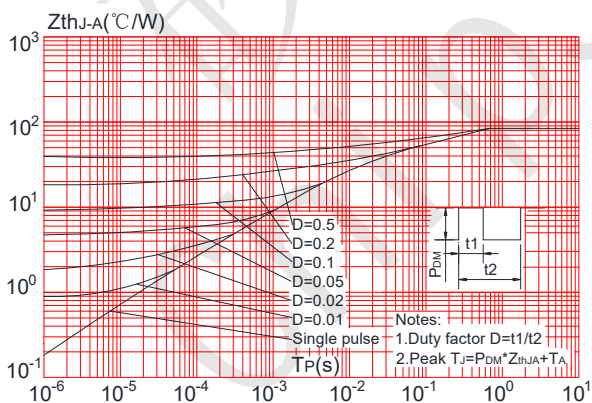
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

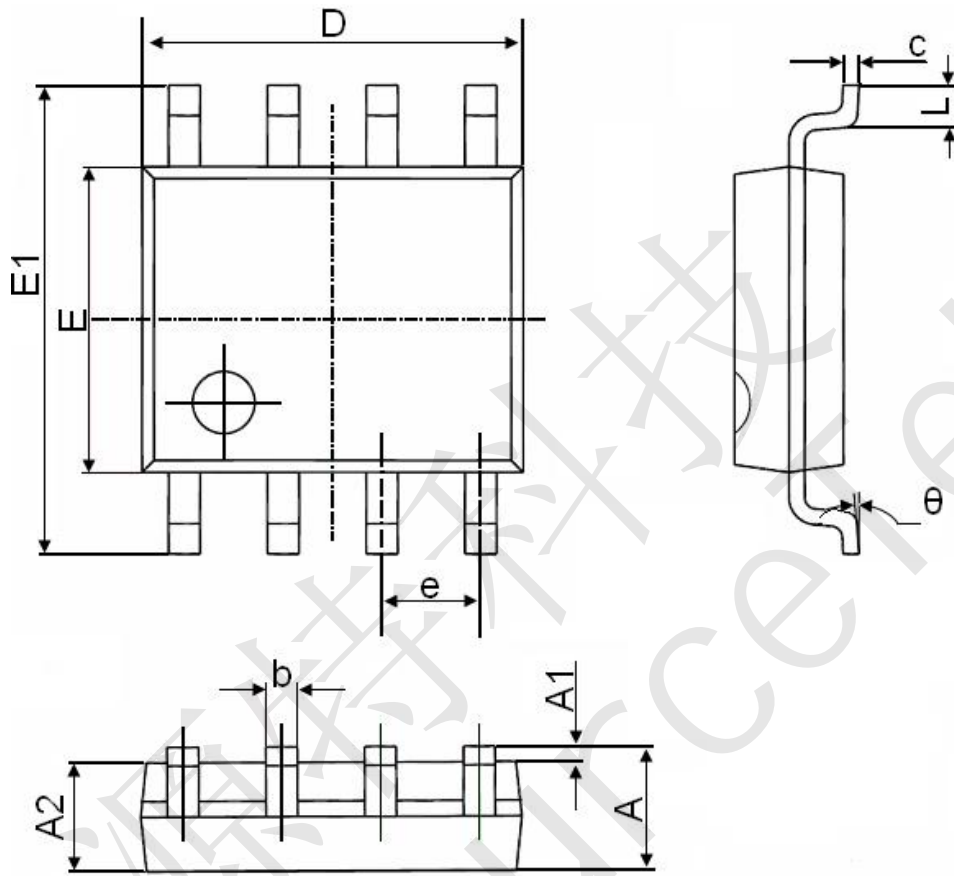


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





#### CST2012S SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°